

# **3SK297**

Silicon N-Channel Dual Gate MOS FET

**HITACHI**

ADE-208-389  
1st. Edition

## **Application**

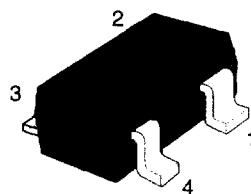
UHF / VHF RF amplifier

## **Features**

- Low noise figure.  
 $NF = 1.0 \text{ dB typ. at } f = 200 \text{ MHz}$
- Capable of low voltage operation

## **Outline**

MPAK-4



1. Source
2. Gate1
3. Gate2
4. Drain

**Absolute Maximum Ratings (Ta = 25°C)**

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DS</sub>	12	V
Gate 1 to source voltage	V <sub>G1S</sub>	±8	V
Gate 2 to source voltage	V <sub>G2S</sub>	±8	V
Drain current	I <sub>D</sub>	25	mA
Channel power dissipation	P <sub>ch</sub>	150	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

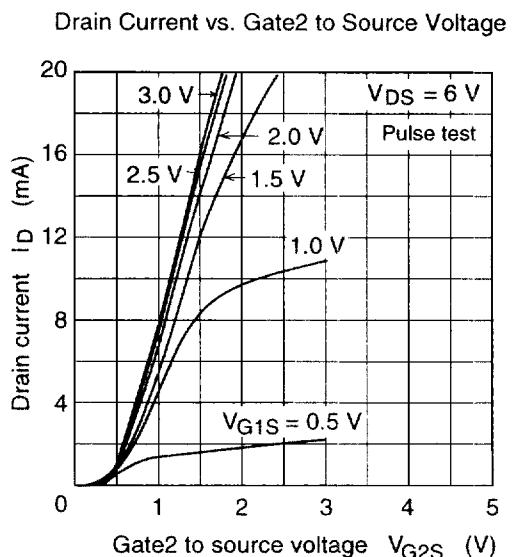
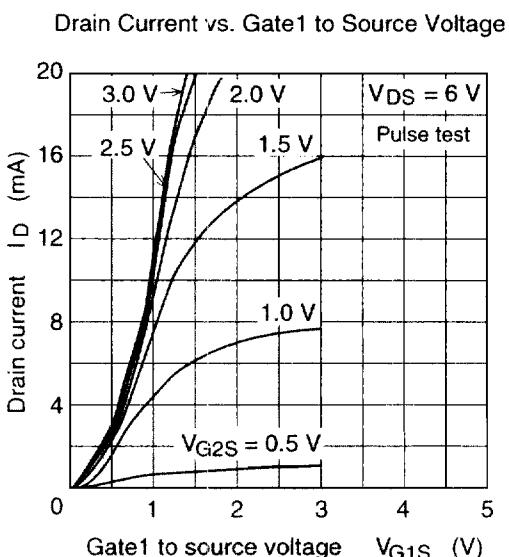
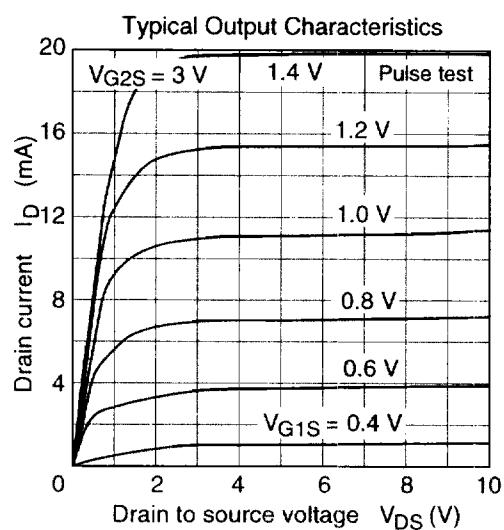
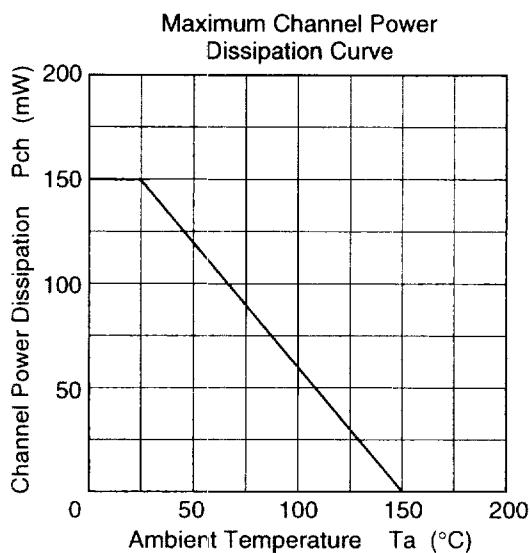
Attention: This device is very sensitive to electro static discharge.

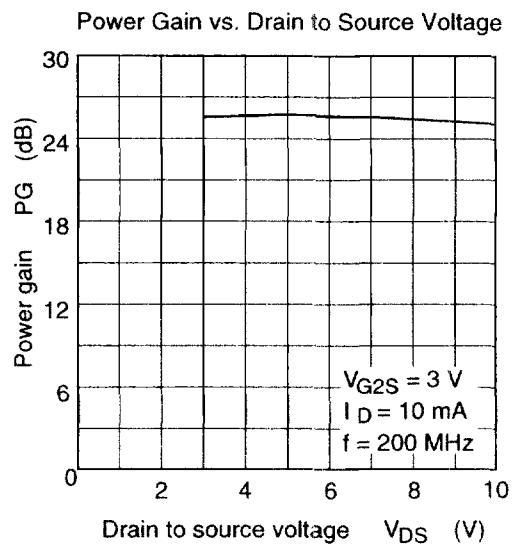
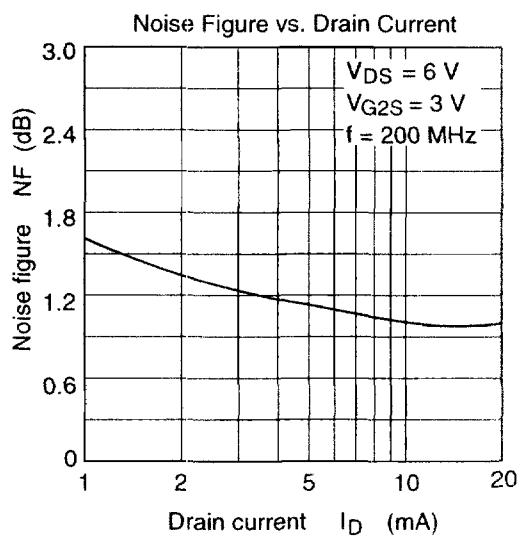
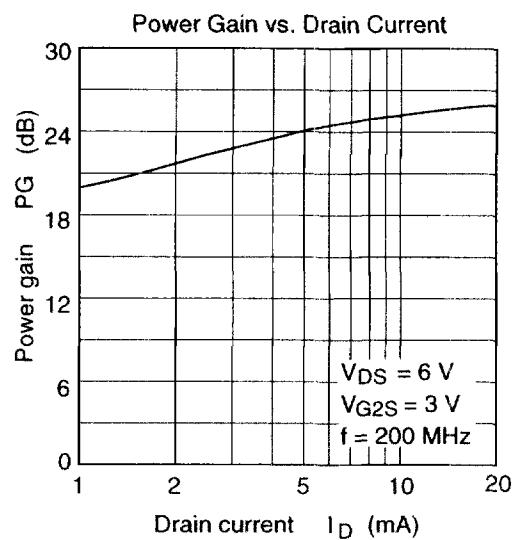
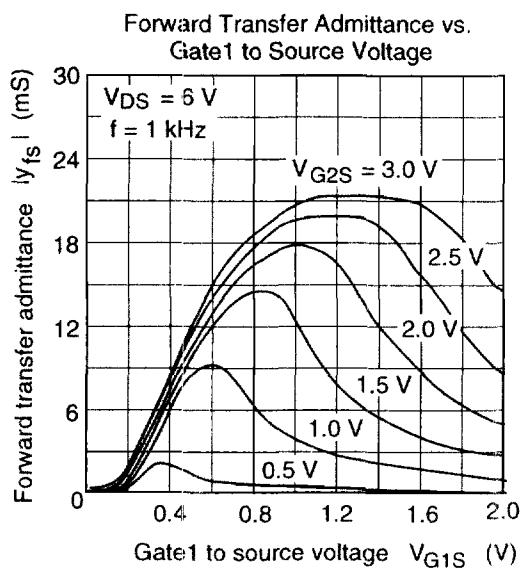
It is recommended to adopt appropriate cautions when handling this transistor.

## Electrical Characteristics (Ta = 25°C)

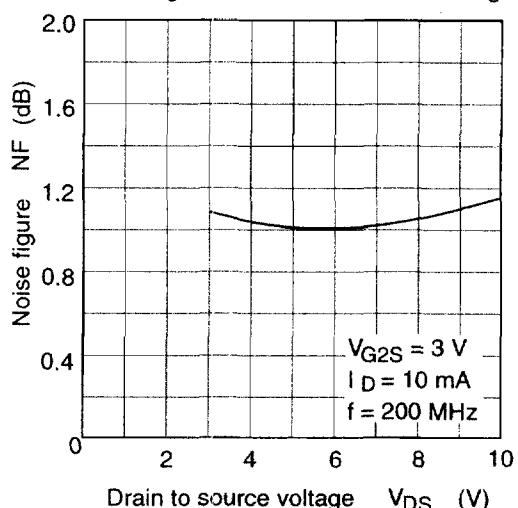
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSX</sub>	12	—	—	V	I <sub>D</sub> = 200 μA, V <sub>G1S</sub> = -3 V, V <sub>G2S</sub> = -3 V
Gate 1 to source breakdown voltage	V <sub>(BR)G1SS</sub>	±8	—	—	V	I <sub>G1</sub> = ±10 μA, V <sub>G2S</sub> = V <sub>DS</sub> = 0
Gate 2 to source breakdown voltage	V <sub>(BR)G2SS</sub>	±8	—	—	V	I <sub>G2</sub> = ±10 μA, V <sub>G1S</sub> = V <sub>DS</sub> = 0
Gate 1 cutoff current	I <sub>G1SS</sub>	—	—	±100	nA	V <sub>G1S</sub> = ±6 V, V <sub>G2S</sub> = V <sub>DS</sub> = 0
Gate 2 cutoff current	I <sub>G2SS</sub>	—	—	±100	nA	V <sub>G2S</sub> = ±6 V, V <sub>G1S</sub> = V <sub>DS</sub> = 0
Drain current	I <sub>DS(on)</sub>	0.5	—	10	mA	V <sub>DS</sub> = 6 V, V <sub>G1S</sub> = 0.75V, V <sub>G2S</sub> = 3 V
Gate 1 to source cutoff voltage	V <sub>G1S(off)</sub>	0	—	+1.0	V	V <sub>DS</sub> = 10 V, V <sub>G2S</sub> = 3V, I <sub>D</sub> = 100 μA
Gate 2 to source cutoff voltage	V <sub>G2S(off)</sub>	0	—	+1.0	V	V <sub>DS</sub> = 10 V, V <sub>G1S</sub> = 3V, I <sub>D</sub> = 100 μA
Forward transfer admittance	y <sub>fs</sub>	16	20	—	mS	V <sub>DS</sub> = 6 V, V <sub>G2S</sub> = 3V, I <sub>D</sub> = 10 mA, f = 1 kHz
Input capacitance	C <sub>iss</sub>	2.4	2.9	3.4	pF	V <sub>DS</sub> = 6 V, V <sub>G2S</sub> = 3V, I <sub>D</sub> = 10 mA, f = 1 MHz
Output capacitance	C <sub>oss</sub>	0.8	1.0	1.4	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	0.023	0.04	pF	
Power gain	PG	22	25	—	dB	V <sub>DS</sub> = 6 V, V <sub>G2S</sub> = 3V, I <sub>D</sub> = 10 mA, f = 200 MHz
Noise figure	NF	—	1.0	1.8	dB	
Power gain	PG	12	15	—	dB	V <sub>DS</sub> = 6 V, V <sub>G2S</sub> = 3V, I <sub>D</sub> = 10 mA, f = 900 MHz
Noise figure	NF	—	3.2	4.5	dB	
Noise figure	NF	—	2.8	3.5	dB	V <sub>DS</sub> = 6 V, V <sub>G2S</sub> = 3V, I <sub>D</sub> = 10 mA, f = 60 MHz

Note: Marking is "ZP—"

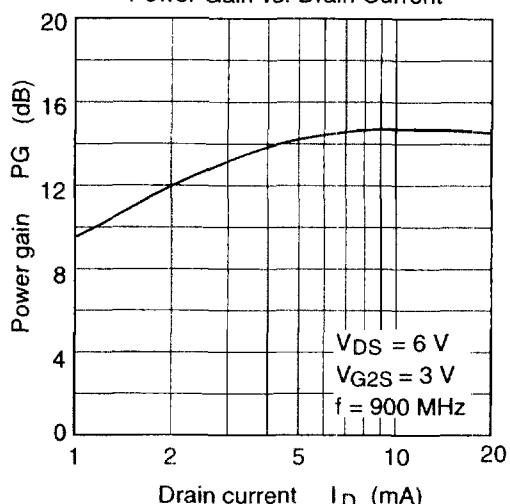




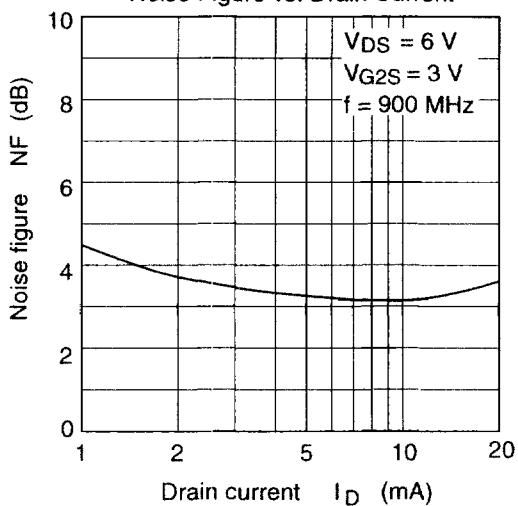
Noise Figure vs. Drain to Source Voltage



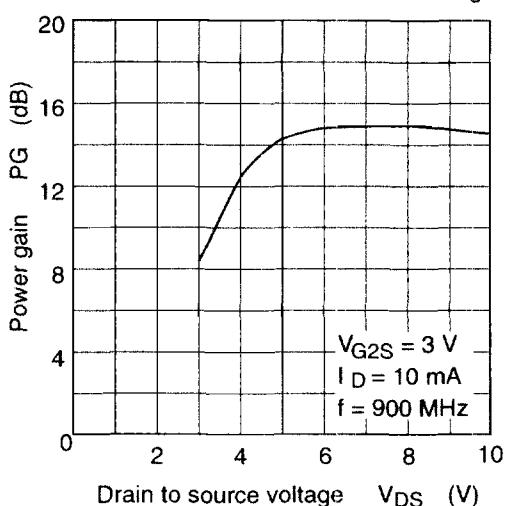
Power Gain vs. Drain Current

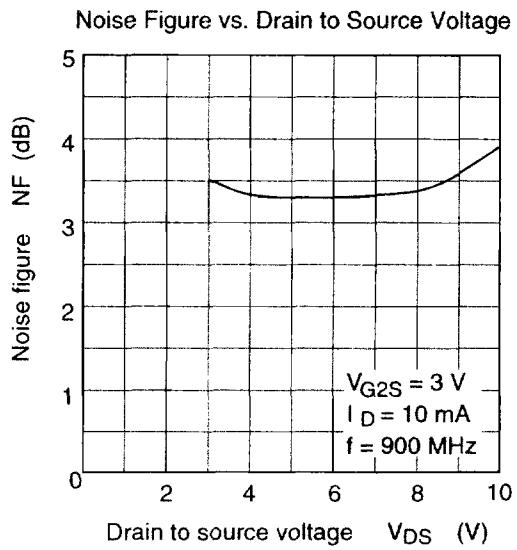


Noise Figure vs. Drain Current

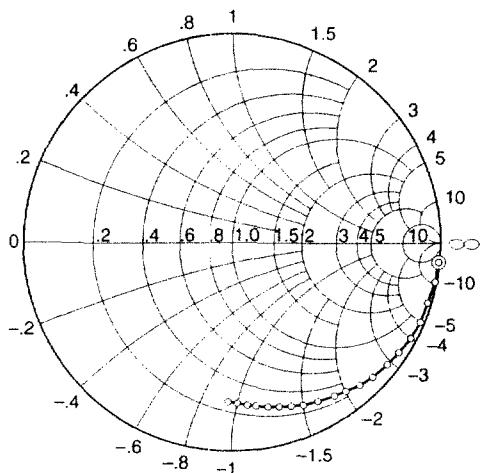


Power Gain vs. Drain to Source Voltage





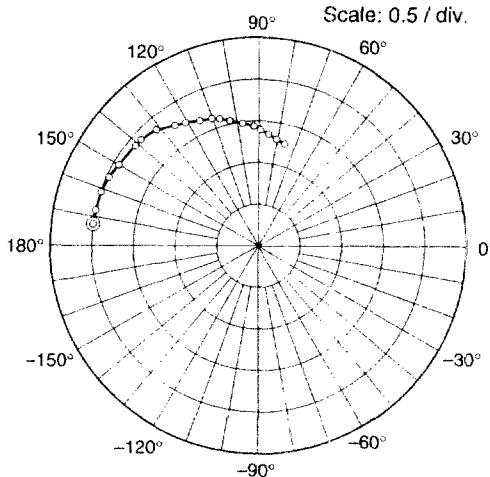
S11 Parameter vs. Frequency



Condition:  $V_{DS} = 6 \text{ V}$ ,  $V_{G2S} = 3 \text{ V}$   
 $I_D = 10 \text{ mA}$ ,  $Z_0 = 50 \Omega$   
50 to 1000 MHz (50 MHz step)



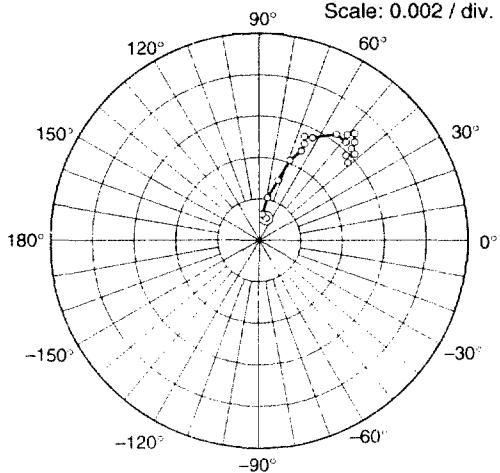
S21 Parameter vs. Frequency



Condition:  $V_{DS} = 6 \text{ V}$ ,  $V_{G2S} = 3 \text{ V}$   
 $I_D = 10 \text{ mA}$ ,  $Z_0 = 50 \Omega$   
50 to 1000 MHz (50 MHz step)



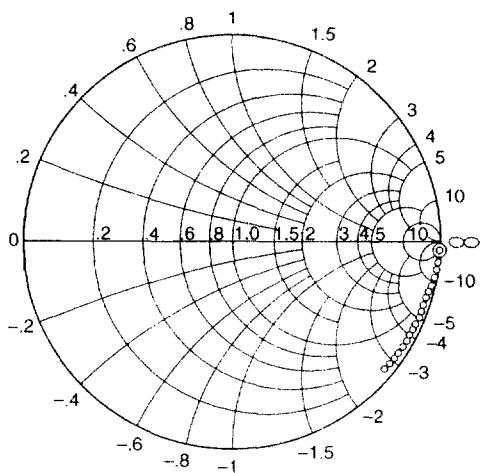
S12 Parameter vs. Frequency



Condition:  $V_{DS} = 6 \text{ V}$ ,  $V_{G2S} = 3 \text{ V}$   
 $I_D = 10 \text{ mA}$ ,  $Z_0 = 50 \Omega$   
50 to 1000 MHz (50 MHz step)



S22 Parameter vs. Frequency



Condition:  $V_{DS} = 6 \text{ V}$ ,  $V_{G2S} = 3 \text{ V}$   
 $I_D = 10 \text{ mA}$ ,  $Z_0 = 50 \Omega$   
50 to 1000 MHz (50 MHz step)



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**3SK297**

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**S Parameter ( $V_{DS} = 6$  V,  $V_{G2S} = 3$  V,  $I_D = 10$  mA,  $Z_0 = 50 \Omega$ )**

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
50	0.994	-5.8	2.04	173.6	0.00116	76.9	0.993	-2.2
100	0.993	-11.0	2.02	167.4	0.00132	85.7	0.993	-4.5
150	0.986	-16.8	2.00	161.5	0.00229	78.2	0.991	-6.4
200	0.980	-22.5	1.98	155.5	0.00313	73.5	0.990	-8.5
250	0.973	-27.8	1.94	149.6	0.00427	68.7	0.987	-10.5
300	0.950	-33.0	1.90	142.6	0.00473	63.9	0.985	-12.5
350	0.936	-38.3	1.86	137.1	0.00536	64.3	0.982	-14.4
400	0.924	-43.4	1.83	131.6	0.00561	64.5	0.979	-16.2
450	0.912	-48.0	1.77	126.8	0.00562	60.9	0.975	-18.2
500	0.893	-52.5	1.71	121.0	0.00640	53.5	0.971	-20.2
550	0.874	-57.3	1.67	115.5	0.00638	49.3	0.967	-22.0
600	0.859	-62.0	1.64	111.1	0.00647	49.0	0.964	-23.9
650	0.846	-66.1	1.58	106.7	0.00667	50.2	0.960	-25.8
700	0.829	-69.8	1.50	102.1	0.00694	49.3	0.955	-27.6
750	0.810	-74.2	1.46	97.1	0.00661	46.6	0.952	-29.4
800	0.802	-78.0	1.44	92.7	0.00618	43.7	0.948	-31.2
850	0.791	-81.6	1.38	88.9	0.00622	44.7	0.944	-33.2
900	0.778	-84.6	1.34	84.2	0.00615	43.6	0.940	-35.1
950	0.756	-88.5	1.30	80.2	0.00576	45.1	0.935	-36.8
1000	0.751	-92.2	1.26	75.9	0.00562	40.7	0.932	-38.5